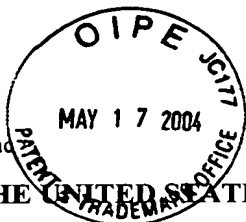


IPW



Docket No. 249687US2/hc

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF: Masakiyo MATSUMURA, et al.

SERIAL NO: 10/790,828

GAU:

FILED: March 3, 2004

EXAMINER:

FOR: CRYSTALLIZATION APPARATUS, CRYSTALLIZATION METHOD, PHASE MODULATION ELEMENT, DEVICE AND DISPLAY APPARATUS

INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR 1.97

COMMISSIONER FOR PATENTS
ALEXANDRIA, VIRGINIA 22313

SIR:

Applicant(s) wish to disclose the following information.

REFERENCES

- ☒ The applicant(s) wish to make of record the references listed on the attached form PTO-1449. Copies of the listed references are attached, where required, as are either statements of relevancy or any readily available English translations of pertinent portions of any non-English language references.
- ☐ A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

RELATED CASES

- ☐ Attached is a list of applicant's pending application(s) or issued patent(s) which may be related to the present application. A copy of the patent(s), together with a copy of the claims and drawings of the pending application(s) is attached along with PTO 1449.
- ☐ A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

CERTIFICATION

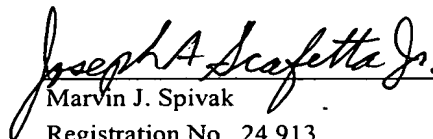
- ☐ Each item of information contained in this information disclosure statement was first cited in any communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this statement.
- ☐ No item of information contained in this information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to the knowledge of the undersigned, having made reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filing of this statement.

DEPOSIT ACCOUNT

- ☒ Please charge any additional fees for the papers being filed herewith and for which no check or credit card payment is enclosed herewith, or credit any overpayment to deposit account number 15-0030. A duplicate copy of this sheet is enclosed.

Respectfully submitted,

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STATEMENT OF RELEVANCY

Reference AM (JP 2000-306859) on Form PTO-1449 is discussed in the specification.

Reference AQ on Form PTO-1449:

Please see Fig. 3 and its description.

Reference AR on Form PTO-1449:

Please see Fig. 2 and its description.

Reference AS on Form PTO-1449:

Please see Fig. 2 and its description.

Reference AT on Form PTO-1449:

The ninth slide.

Reference AU on Form PTO-1449 is discussed in the specification.

Reference AV on Form PTO-1449 is discussed in the specification.

Form PTO 1449
(Modified)U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICE

ATTY DOCKET NO.

249687US2

SERIAL NO.

10/790,828

LIST OF REFERENCES CITED BY APPLICANT

APPLICANT

Masakiyo MATSUMURA, et al.

FILING DATE

March 3, 2004

GROUP

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	AA					
	AB					
	AC					
	AD					
	AE					
	AF					
	AG					
	AH					
	AI					
	AJ					
	AK					
	AL					

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION	
				YES	NO
	AM 2000-306859	11/02/2000	JAPAN (with corr. EP 1 047 119)		X
	AN 1 047 119	10/25/2000	EUROPE		
	AO				
	AP				

OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)

OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)		
AQ	C-H. OH, et al., Japanese Journal of Applied Physics, vol. 37, part 2, no. 5A, pages L492 - L495, "A NOVEL PHASE-MODULATED EXCIMER-LASER CRYSTALLIZATION METHOD OF SILICON THIN FILMS", May 1, 1998	
AR	M. NAKATA, et al., Japanese Journal of Applied Physics, vol. 40, part 1, no. 5A, pages 3049-3054, "A NEW NUCLEATION-SITE-CONTROL EXCIMER-LASER-CRYSTALLIZATION METHOD", May 2001	
AS	M. MATSUMURA, IDW '02 AMD5-1, pages 263-266, "ADVANCED LASER-CRYSTALLIZATION TECHNOLOGIES OF Si FOR HIGH-PERFORMANCE TFTs", 2001	
AT	International Display Workshops, pages 1-6, "ADVANCED LASER-CRYSTALLIZATION TECHNOLOGIES OF Si FOR HIGH-PERFORMANCE TFTs", 2002	
AU	M. MATSUMURA, Journal of The Surface Science Society of Japan, vol. 21, no. 5, pages 278-287, "PREPARATION OF ULTRA-LARGE GRAIN SILICON THIN-FILMS BY EXCIMER-LASER", May 2000	
AV	K. INOUE, et al., The Institute of Electronics, Information and Communication Engineers Transactions, vol. J85-C, no. 8, pages 624-629, "AMPLITUDE AND PHASE MODULATED EXCIMER-LASER MELT-REGROWTH METHOD OF SILICON THIN-FILMS - A NEW GROWTH METHOD OF 2-D POSITION-CONTROLLED LARGE - GRAINS", August 2002	<input type="checkbox"/> Additional References sheet(s) attached
		Date Considered

Examiner

*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.